

Table of Contents

Preface

Committeess

I. Multi-Crystalline Silicon for Solar Cells

Influence of Defects on Solar Cell Characteristics

O. Breitenstein, J. Bauer, P.P. Altermatt and K. Ramspeck 1

Dislocation Engineering in Multicrystalline Silicon

M.I. Bertoni, C. Colin and T. Buonassisi 11

Grain Boundaries in Multicrystalline Si

J. Chen, B. Chen, W. Lee, M. Fukuzawa, M. Yamada and T. Sekiguchi 19

Analysis of Heterogeneous Iron Precipitation in Multicrystalline Silicon

A. Haarahiltunen, V. Vähänissi, M. Yli-Koski, H. Talvitie and H. Savin 27

Growth of Silicon Carbide Filaments in Multicrystalline Silicon for Solar Cells

H.J. Möller, C. Funke, J. Bauer, S. Köstner, H. Straube and O. Breitenstein 35

Analysis of Silicon Carbide and Silicon Nitride Precipitates in Block Cast Multicrystalline Silicon

M. Holla, T. Arguirov, W. Seifert and M. Kittler 41

Investigations on the Behaviour of Carbon during Inductive Melting of Multicrystalline Silicon

L. Raabe, J. Ehrig, S. Würzner, O. Pätzold, M. Stelter and H.J. Möller 49

An Investigation into Fracture of Multi-Crystalline Silicon

B.R. Mansfield, D.E.J. Armstrong, P.R. Wilshaw and J.D. Murphy 55

II. Advanced Semiconductor Materials: Strained Si, SOI, SiGe, SiC

Strained Silicon Devices

M. Reiche, O. Moutanabbir, J. Hoentschel, U.M. Gösele, S. Flachowsky and M. Horstmann 61

Novel Trends in SOI Technology for CMOS Applications

O. Kononchuk, D. Landru and C. Veytizou 69

Advanced Si-based Semiconductors for Energy and Photonic Applications

J. Kouvetakis, J. Menendez and J. Tolle 77

Si Wafer Bonding: Structural Features of the Interface

V.I. Vdovin, N.D. Zakharov, E. Pippel, P. Werner, M.G. Milvidskii, M. Ries, M. Seacrist and R.J. Falster 85

Buried Insulating Layer Formation in Cz Si Wafers after Helium Implantation, Nitrogen Plasma Treatment and Annealing

N.V. Frantskevich, A.V. Frantskevich, A.K. Fedotov and A.V. Mazanik 91

Growth of Heavily Phosphorus-Doped (111) Silicon Crystals

F. Liu, H.P. Han, Y.M. Wang and L.Y. Tong 95

Semi-Insulating Silicon for Microwave Devices

D.M. Jordan, K. Mallik, R.J. Falster and P.R. Wilshaw 101

III. Impurities (Oxygen, Carbon, Nitrogen, Metals) and Point Defects in Si and SiGe

Can Impurities be Beneficial to Photovoltaics?

A. Luque and A. Martí 107

Properties of Fast-Diffusing Oxygen Species in Silicon Deduced from the Generation Kinetics of Thermal Donors

V.V. Voronkov, G.I. Voronkova, A.V. Batunina, V.N. Golovina, R.J. Falster, M. Cornara, N.B. Tiurina and A.S. Guliaeva 115

The Production of Vacancy-Oxygen Defects in Electron-Irradiated Cz-Si Initially Treated at High Temperatures and High Pressures

A. Andrianakis, C.A. Londos, A. Misiuk, V.V. Emtsev, G.A. Oganessian and H. Ohyama 123

Divacancy-Oxygen and Trivacancy-Oxygen Complexes in Silicon: Local Vibrational Mode Studies	
L.I. Murin, B.G. Svensson, J.L. Lindström, V.P. Markevich and C.A. Londos	129
Low-Temperature Elastic Softening due to Vacancies in Boron-Doped FZ Silicon Crystals	
H. Yamada-Kaneta, H. Watanabe, Y. Nagai, S. Baba, M. Akatsu, Y. Nemoto and T. Goto	135
Vacancies and Self-Interstitials Dynamics in Silicon Wafers	
O. Caha, J. Kuběna, A. Kuběna and M. Meduňa	139
Interaction of Point Defects with Impurities in the Si-SiO₂ System and its Influence on the Properties of the Interface	
D. Kropman, E. Mellikov, K. Lott, T. Kärner, I. Heinmaa, T. Laas, A. Medvid, W. Skorupa, S. Prucnal, S. Zvyagin, E. Cizmar, M. Ozerov and J. Woznitsa	145
Anomalous Out-Diffusion Profiles of Nitrogen in Silicon	
V.V. Voronkov, R.J. Falster and S. Senkader	149
DLTS Studies of Carbon Related Complexes in Irradiated N- and P-Silicon	
L.F. Makarenko, F.P. Korshunov, S.B. Lastovskii, L.I. Murin and M. Moll	155
Copper In-Depth Distribution in Hydrogen Implanted Cz Si Wafers Subjected to Two-Step Annealing	
A.V. Frantskevich, A.K. Fedotov, A.V. Mazanik and N.V. Frantskevich	161
Radiation Defects in Silicon: Effect of Contamination by Platinum Atoms	
P. Hazdra and V.V. Komarnitsky	167
Review of Stress Effects on Dopant Solubility in Silicon and Silicon-Germanium Layers	
N.S. Bennett, C. Ahn, N.E.B. Cowern and P. Pichler	173
Oxygen Diffusion in Si_{1-x}Ge_x Alloys	
L.I. Khirunencko, Y.V. Pomozov, M.G. Sosnin, A.V. Duvanskii, S.K. Golyk, N.V. Abrosimov and H. Riemann	181
The Effect of Germanium Doping on the Production of Carbon-Related Defects in Electron-Irradiated Czochralski Silicon	
C.A. Londos, A. Andrianakis, D. Aliprantis, E.N. Sgourou, V.V. Emtsev and H. Ohyama	187
 IV. Modeling and Simulation of Growth, Gettering and Characterization	
Numerical Analysis of mc-Si Crystal Growth	
K. Kakimoto, H. Matsuo, S. Hisamatsu, B. Ganesh, B. Gao, X.J. Chen, L.J. Liu, H. Miyazawa and Y. Kangawa	193
Molecular Simulation on Interfacial Structure and Gettering Efficiency of Si (110)/(100) Directly Bonded Hybrid Crystal Orientation Substrates	
H. Kariyazaki, T. Aoki, K. Izunome and K. Sueoka	199
Optimization of Silicon Ingot Quality by the Numerical Prediction of Bulk Crystal Defects	
F. Loix, F. Dupret, A. de Potter, R. Rolinsky, N. Van den Bogaert and V. Regnier	205
Rate Equation Modeling, Ab Initio Calculation, and High Sensitive FTIR Investigations of the Early Stages of Oxide Precipitation in Vacancy-Rich CZ Silicon	
G. Kissinger, J. Dabrowski, V.D. Akhmetov, A. Sattler, D. Kot and W. von Ammon	211
Thermal Optimization of Cz Silicon Single Crystal Growth	
A.I. Prostomolotov, N.A. Verezub and M.G. Milvidskii	217
Simulation of Iron Distribution after Crystallization of mc Silicon	
J. Schön, H. Habenicht, M.C. Schubert and W. Warta	223
Comparison of Efficiency and Kinetics of Phosphorus-Diffusion and Aluminum Gettering of Metal Impurities in Silicon: a Simulation study	
M.A. Falkenberg, D. Abdelbarey, V.V. Kveder and M. Seibt	229
Effect of Growth Conditions and Catalyst Material on Nanowhisker Morphology: Monte Carlo Simulation	
A.G. Nastovjak, I.G. Neizvestny and N. Shwartz	235
Versatile Simulation Tool and Novel Measurement Method for Electrical Characterization of Semiconductors	
N. Schöler, T. Hahn, K. Dornich and J.R. Niklas	241
Simulation of XBIC Contrast of Precipitates in Si	
E.B. Yakimov	247

V. Defect Aspects and Defect Engineering

Dislocation Nucleation in Heteroepitaxial Semiconducting Films B. Pichaud, N. Burle, M. Texier, C. Fontaine and V.I. Vdovin	251
Impurity Engineering of Czochralski Silicon J.H. Chen, X.Y. Ma and D.R. Yang	261
The Role of the Interstitial Oxygen in the Recovery and Evolution of the Boron Implantation Damage I. Mica, M.L. Polignano, F. Cazzaniga, L. Di Piazza, M. Mariani, E. Ricci, F. Sammiceli and S. Speranza	269
Oxygen Precipitation in Conventional and Nitrogen Co-Doped Heavily Arsenic-Doped Czochralski Silicon Crystals: Oswald Ripening X.Y. Ma, Y. Feng, Y.H. Zeng and D.R. Yang	275
Study of the Mechanisms of Oxygen Precipitation in RTA Annealed Cz-Si Wafers V.G. Litovchenko, I.P. Lisovskyy, M. Voitovych, A. SARIKOV, S.O. Zlobin, V.P. Kladko and V. Machulin	279
Electronic States of Oxygen-Free Dislocation Networks Produced by Direct Bonding of Silicon Wafers M. Trushin, O.F. Vyvenko, T. Mchedlidze, O. Kononchuk and M. Kittler	283
Dislocation States and Deformation-Induced Point Defects in Plastically Deformed Germanium S. Shevchenko and A.N. Tereshchenko	289
Defect Generation during Plastic Deformation of Si-Rich Cz-Grown SiGe Crystals N. Yarykin and N.V. Abrosimov	295
Formation of Radiation-Induced Defects in Si Crystals Irradiated with Electrons at Elevated Temperatures V.P. Markevich, A.R. Peaker, S.B. Lastovskii, V.E. Gusakov, I.F. Medvedeva and L.I. Murin	299
Role of Ion Irradiation Induced Lattice Defects on Nanoscale Capacitive Behavior of Graphene S. Sonde, F. Giannazzo, V. Raineri, S. Di Franco, A. Marino and E. Rimini	305
Boron and Phosphorus Implantation Induced Electrically Active Defects in p-Type Silicon J. Senawiratne, J.S. Cites, J.G. Couillard, J. Moll, C.A. Kosik Williams and P.G. Whiting	313
Accumulation of Hydrogen within Implantation-Damaged Areas in Processed Si:N and Si:O A. Misiuk, A.G. Ulyashin, A. Barcz and P. Formanek	319
Influence of Hydrogen on the Structural Stability of Annealed Ultrathin Si/Ge Amorphous Layers C. Frigeri, L. Nasi, M. Serényi, A. Csik, Z. Erdélyi and D.L. Beke	325
Demonstration of Defect-Induced Limitations on the Properties of Au/3C-SiC Schottky Barrier Diodes J. Eriksson, M.H. Weng, F. Roccaforte, F. Giannazzo, S. Leone and V. Raineri	331
Suppression of Pores Formation on a Surface of p-Si by Laser Radiation A. Medvid, P. Onufrijevs, L. Fedorenko, N. Yusupov and E. Dauksta	337

VI. Gettering and Hydrogen Passivation

Hydrogenation in Crystalline Silicon Materials for Photovoltaic Application G. Hahn, M. Käs and B. Herzog	343
Hydrogen-Induced Passivation of Grain-Boundary Defects in Polycrystalline Silicon N.H. Nickel	351
Bulk Passivation of Defects in Multi-Crystalline Silicon Solar Cells by a-SiN_x:H Layers E. Cornagliotti, H.F.W. Dekkers, C. Prastani, J. John, E. Van Kerschaver, J. Poortmans and R.P. Mertens	357
Passivation of Si Surfaces Investigated by <i>In Situ</i> Photoluminescence Techniques J. Rappich, X. Zhang, D.M. Rosu, U. Schade and K. Hinrichs	363
Gettering Efficiency of Si (110)/(100) Directly Bonded Hybrid Crystal Orientation Substrates T. Aoki, H. Kariyazaki, K. Sueoka and K. Izunome	369
Trans-R_p Gettering and Out-Diffusion of Oxygen Implanted into Highly B-Doped Silicon R. Kögler, C. Dubois, J.W. Gerlach, H. Hutter, A. Mücklich and W. Skorupa	375

Iron Gettering in CZ Silicon during the Industrial Solar Cell Process A. Laades, K. Lauer, C. Maier, D. Alber, M. Bähr, J. Nutsch, J. Lossen and A. Lawerenz	381
Study of Internal versus External Gettering of Iron during Slow Cooling Processes for Silicon Solar Cell Fabrication J. Hofstetter, J.F. Lelièvre, C. del Cañizo and A. Luque	387
Effect of Oxygen in Low Temperature Boron and Phosphorus Diffusion Gettering of Iron in Czochralski-Grown Silicon V. Vähäniissi, A. Haarahiltunen, H. Talvitie, M.I. Asghar, M. Yli-Koski and H. Savin	395
Far-Action Defects Formation and Gettering in 6H-SiC Lely Crystals Irradiated by Bi D.B. Shustov, E.V. Kolesnikova, E.V. Kalinina, V.A. Skuratov and M.V. Zamoryanskaya	401

VII. Defect and Impurity Characterization

Quantitative Iron Concentration Imaging M.C. Schubert, H. Habenicht, M.J. Kerler and W. Warta	407
EBIC Investigation of the Influence of Hydrogen Passivation on Thin-Film Polycrystalline Silicon Solar Cells Obtained by Aluminium Induced Crystallization and Epitaxy D. Van Gestel, I. Gordon and J. Poortmans	413
Characterization of Thin Film Photovoltaic Material Using Photoluminescence and Raman Spectroscopy T. Mchedlidze, T. Arguirov, S. Kouteva-Arguirova and M. Kittler	419
Comparative Study of Electrical and Optical Properties of Plastically Deformed Silicon N. Yarykin and O.V. Feklisova	425
Spatially Resolved Defect Analysis in Cz-Silicon after Copper-Nickel Co-Precipitation by Virtue of Light-Beam-Induced Current Measurements P. Saring, C. Rudolf, L. Stolze, A. Falkenberg and M. Seibt	431
<i>In Situ</i> Observation of Oxygen Precipitation in Silicon with High Energy X-Rays H. Grillenberger and A. Magerl	437
Delineation of Microdefects in Silicon Substrates by Chromium-Free Preferential Etching Solutions and Laser Scattering Tomography M. Pellowska, D. Possner, D. Kot, G. Kissinger and B.O. Kolbesen	443
An Express Method for the Study of Planar Homogeneity of Diffusion Length in Multicrystalline Solar Silicon V.G. Litovchenko, A. SARIKOV and A.A. Evtukh	449
Point Defects in γ-Irradiated Germanium: High- and Low- Momentum Positron Annihilation Study Before and After n-p-Conversion N.Y. Arutyunov, V.V. Emtsev and R. Krause-Rehberg	455
Electron-Beam-Induced Current Study of Breakdown Behavior of High-K Gate MOSFETs J. Chen, T. Sekiguchi, M. Takase, N. Fukata, R. Hasunuma, K. Yamabe, M. Sato, K. Yamada and T. Chikyo	461
Characterization of Semiconductor Films Epitaxially Grown on Thin Metal Oxide Buffer Layers P. Zaumseil, A. Giussani, O. Seifarth, T. Arguirov, M.A. Schubert and T. Schroeder	467
SEM Characterization of Silicon Layers Grown on Carbon Foil S.K. Brantov, A.V. Eltzov, O.V. Feklisova and E.B. Yakimov	473
Investigation of the Mechanical Properties of Thin Films by Bulge Test A. Hémel, A. Jacques, T. Schenk and T. Kruml	477
Defect Characterization of Poly-Ge and VFG-Grown Ge Material M. Holla, T. Arguirov, G. Jia, M. Kittler, C. Frank-Rotsch, F.M. Kiessling and P. Rudolph	483
Cathodoluminescence of SiO₂/Si System M.V. Zamoryanskaya	487
Correlation Study of Morphology, Electrical Activation and Contact formation of Ion Implanted 4H-SiC M.H. Weng, F. Roccaforte, F. Giannazzo, S. Di Franco, C. Bongiorno, E. Zanetti, A. Ruggiero, M. Saggio and V. Raineri	493

VIII. Nanostructures and New Devices

Current Status of Graphene Transistors M.C. Lemme	499
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Theoretical Study of Ionized Impurities in Silicon Nanowire MOS Transistors M. Bescond, M. Lannoo, L. Raymond and F. Michelini	511
Scaling in Quantum Transport in Silicon Nano-Transistors U. Wulf and H. Richter	517
Anisotropic Strain – Anisotropic Heating Engineering for Silicon Nanocrystals in SiO₂ I.V. Antonova, D.V. Marin, V.A. Volodin, V.A. Skuratov, J. Jedrzejewski and I. Balberg	523
Silicon Cluster Aggregation in Silica Layers H.J. Fitting, L. Fitting Kourkoutis, R. Salh, E.V. Kolesnikova, M.V. Zamoryanskaya, A. von Czarnowski and B. Schmidt	529
Feedback Effect on the Self-Organized Nanostructures Formation on Silicon upon Femtosecond Laser Ablation O. Varlamova, M. Ratzke and J. Reif	535
Confinement Levels in Passivated SiGe/Si Quantum Well Structures I.V. Antonova, E.P. Neustroev, S.A. Smagulova, M.S. Kagan, P.S. Alekseev, S.K. Ray, N. Sustersic and J. Kolodzey	541
 IX. Silicon-Based Photonics and Defect Luminescence	
Silicon Periodic Structures and their Liquid Crystal Composites E.V. Astrova, V.A. Tolmachev, Y.A. Zharova, G.V. Fedulova, A.V. Baldycheva and T.S. Perova	547
Dependence of Luminescence Properties of Bonded Si Wafers on Surface Orientation and Twist Angle. E.A. Steinman, O. Kononchuk, A.N. Tereshchenko and A.A. Mazilkin	555
D-Line Emission from Small Angle Grain Boundaries in Multicrystalline Si T. Sekiguchi, W. Lee, J. Chen and B. Chen	561
Determination of the Origin of Dislocation Related Luminescence from Silicon Using Regular Dislocation Networks T. Mchedlidze, O. Kononchuk, T. Arguirov, M. Trushin, M. Reiche and M. Kittler	567
Structural and Luminescent Properties of Implanted Silicon Layers with Dislocation-Related Luminescence N.A. Sobolev, Kalyadin, R.N. Kyutt, E.I. Shek and V.I. Vdovin	573
Optimization of the Luminescence Properties of Silicon Diodes Produced by Implantation and Annealing T. Arguirov, T. Mchedlidze, M. Reiche and M. Kittler	579